Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

## 2SC4209

# Driver Stage Amplifier Applications Voltage Amplifier Applications

• Complementary to 2SA1620

### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	80	V
Collector-emitter voltage	V <sub>CEO</sub>	80	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	Ic	300	mA
Base current	Ι <sub>Β</sub>	60	mA
Collector power dissipation	PC	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

# 1. BASE 2. EMITTER 3. COLLECTOR JEDEC TO-236MOD JEITA SC-59 TOSHIBA 2-3F1A

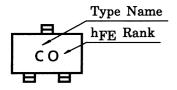
### Weight: 0.012 g (typ.)

### **Electrical Characteristics (Ta = 25°C)**

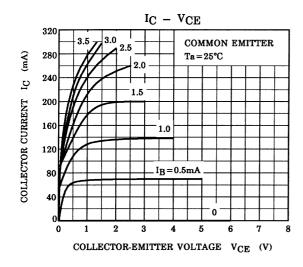
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 5 \text{ V}, I_{C} = 0$	_	_	0.1	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = 5 \text{ mA}, I_B = 0$	80	_	_	V
DC current gain	h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 50 mA	70	_	240	
	h <sub>FE (2)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 200 mA	40	_		
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_C = 200 \text{ mA}, I_B = 10 \text{ mA}$	_	_	0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = 2 \text{ V}, I_{C} = 5 \text{ mA}$	0.55	_	0.8	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 10 mA	_	100	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	10	_	pF

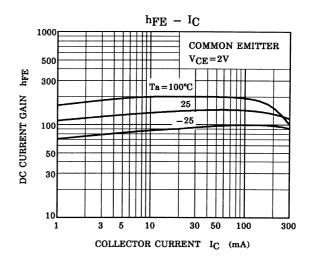
Note:  $h_{FE}$  (1) classification O: 70~140, Y: 120~240

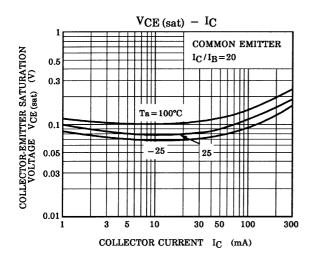
### Marking

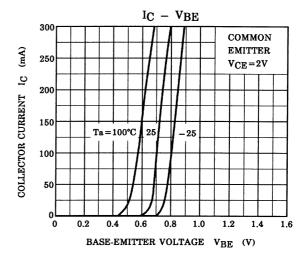


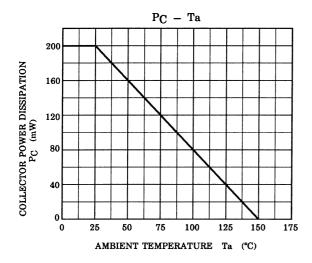
1 2003-03-27











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